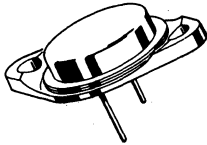


**2N4913 (SILICON)**  
**2N4914**  
**2N4915**

NPN power transistors for use in power amplifier and switching circuits. Complement to PNP 2N4904 thru 2N4906.



**CASE 11  
(TO-3)**

Collector connected to case

**MAXIMUM RATINGS**

Rating	Symbol	2N4913	2N4914	2N4915	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	60	80	Vdc
Collector-Base Voltage	$V_{CB}$	40	60	80	Vdc
Emitter-Base Voltage	$V_{EB}$	5.0			Vdc
Collector Current - Continuous	$I_C$	5.0			A dc
Base Current - Continuous	$I_B$	1.0			A dc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	87.5			Watts
		0.5			W/ $^\circ\text{C}$
Operating & Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200			$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$\theta_{JC}$	2.0	$^\circ\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Fig. No.	Symbol	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Sustaining Voltage <sup>(1)</sup> ( $I_C = 0.2 \text{ A dc}, I_B = 0$ )	2N4913 2N2914 2N4915	11	$BV_{CEO(sus)}$	40 60 80	- - -	Vdc
Collector Cutoff Current ( $V_{CE} = \text{Rated } V_{CEO}, I_B = 0$ )			$I_{CEO}$	-	1.0	mAdc
Collector Cutoff Current ( $V_{CE} = \text{Rated } V_{CEO}, V_{EB(off)} = 1.5 \text{ Vdc}$ ) ( $V_{CE} = \text{Rated } V_{CEO}, V_{EB(off)} = 1.5 \text{ Vdc}, T_C = 150^\circ\text{C}$ )		5, 6	$I_{CEX}$	- -	1.0 2.0	mAdc
Collector Cutoff Current ( $V_{CB} = \text{Rated } V_{CB}, I_E = 0$ )		5, 6	$I_{CBO}$	-	1.0	mAdc
Emitter Cutoff Current ( $V_{EB} = 5.0 \text{ Vdc}, I_C = 0$ )			$I_{EBO}$	-	1.0	mAdc

**ON CHARACTERISTICS <sup>(1)</sup>**

DC Current Gain ( $I_C = 2.5 \text{ A dc}, V_{CE} = 2.0 \text{ Vdc}$ ) ( $I_C = 5.0 \text{ A dc}, V_{CE} = 2.0 \text{ Vdc}$ )	1	$h_{FE}$	25 7.0	100 -	-
Collector-Emitter Saturation Voltage ( $I_C = 2.5 \text{ A dc}, I_B = 250 \text{ mA dc}$ ) ( $I_C = 5.0 \text{ A dc}, I_B = 1.0 \text{ A dc}$ )	2, 3, 4	$V_{CE(sat)}$	- -	1.0 1.5	Vdc
Base-Emitter On Voltage ( $I_C = 2.5 \text{ A dc}, V_{CE} = 2.0 \text{ Vdc}$ )	3, 4	$V_{BE(on)}$	-	1.4	Vdc

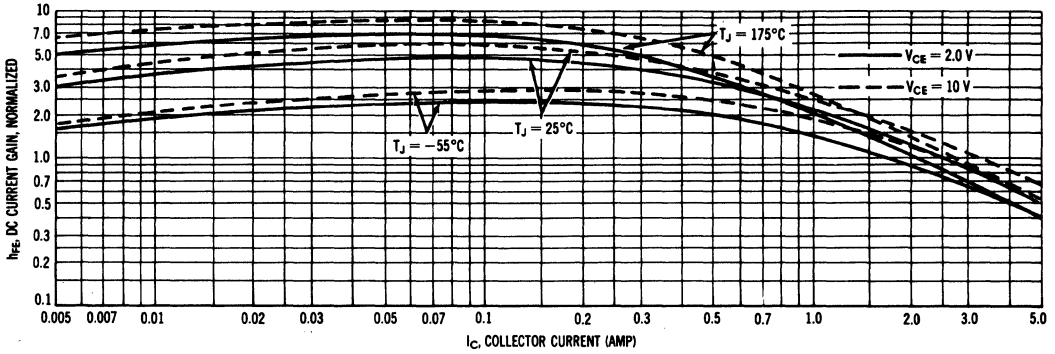
**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain-Bandwidth Product ( $I_C = 1.0 \text{ A dc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ MHz}$ )		$f_T$	4.0	-	MHz
Small-Signal Current Gain ( $I_C = 500 \text{ mA dc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$ )		$h_{fe}$	20	-	-

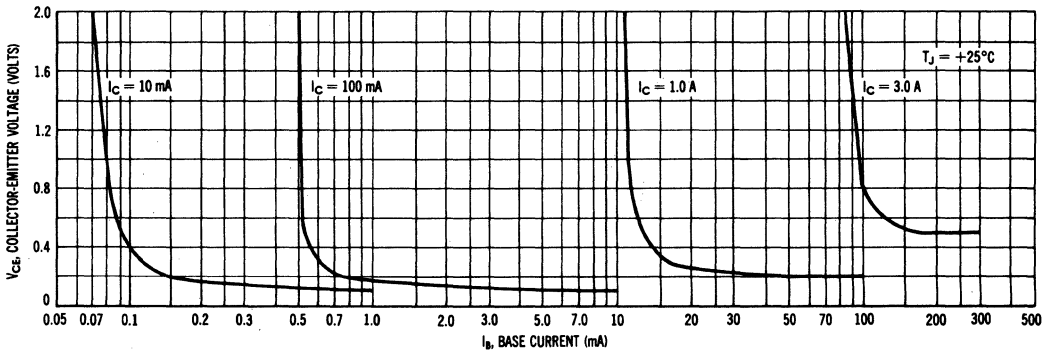
<sup>(1)</sup> Pulse Test,  $PW \approx 300 \mu\text{s}$ , Duty Cycle  $\approx 2.0\%$

**2N4913, 2N4914, 2N4915 (continued)**

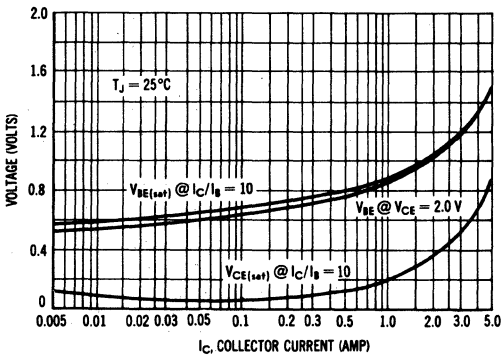
**FIGURE 1 — NORMALIZED DC CURRENT GAIN**



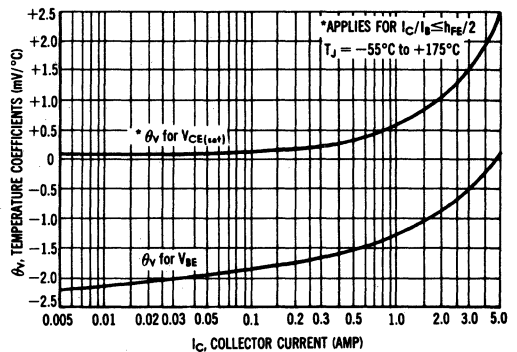
**FIGURE 2 — COLLECTOR SATURATION REGION**



**FIGURE 3 — "ON" VOLTAGES**



**FIGURE 4 — TEMPERATURE COEFFICIENTS**



# 2N4913, 2N4914, 2N4915 (continued)

## TYPICAL "OFF" REGION CHARACTERISTICS

FIGURE 5 — CUT-OFF REGION

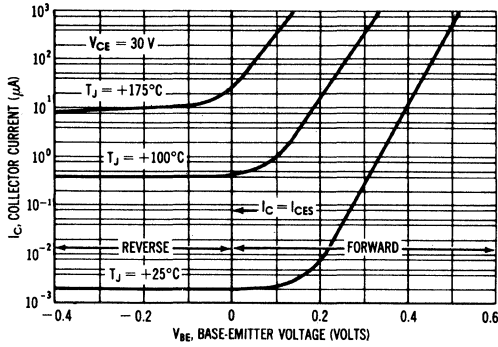


FIGURE 6 — EFFECTS OF BASE-EMITTER RESISTANCE

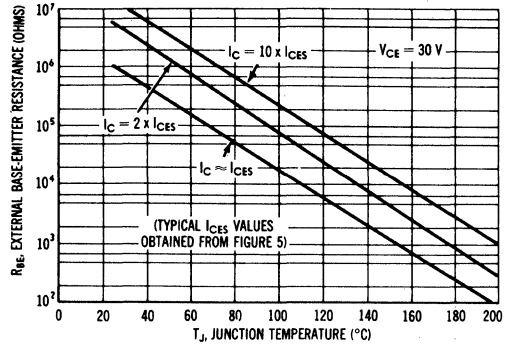


FIGURE 7 — SWITCHING TIME EQUIVALENT CIRCUIT

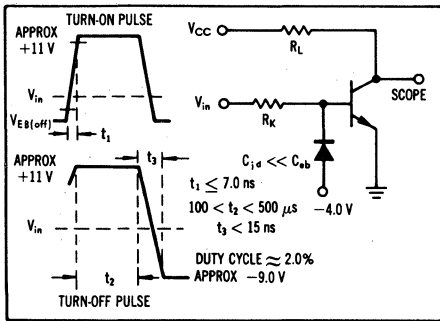


FIGURE 8 — CAPACITANCE

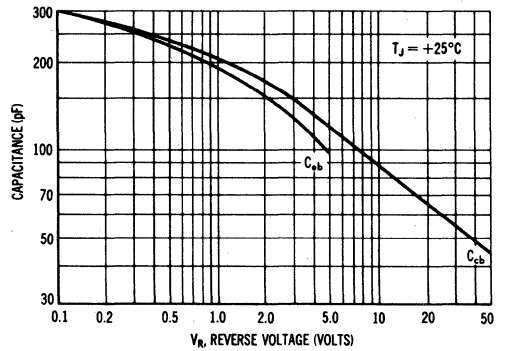


FIGURE 9 — TURN-ON TIME

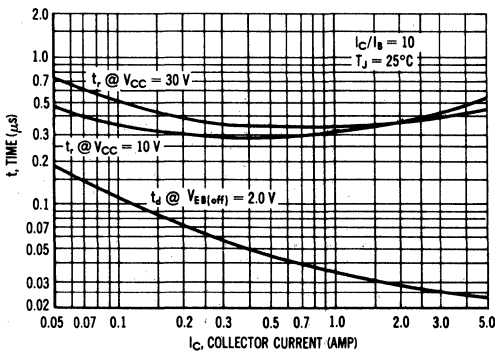
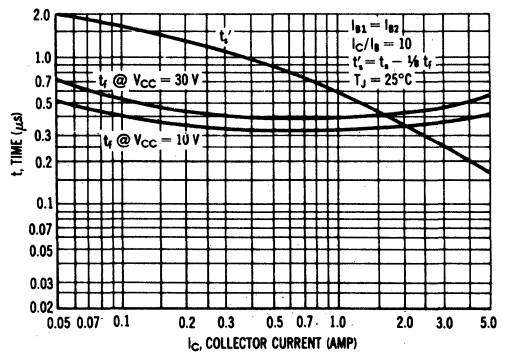


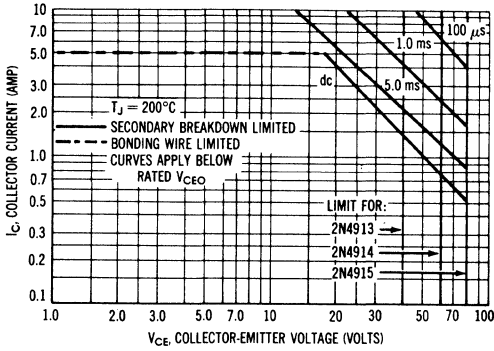
FIGURE 10 — TURN-OFF TIME



2N4913, 2N4914, 2N4915 (continued)

RATING AND THERMAL DATA

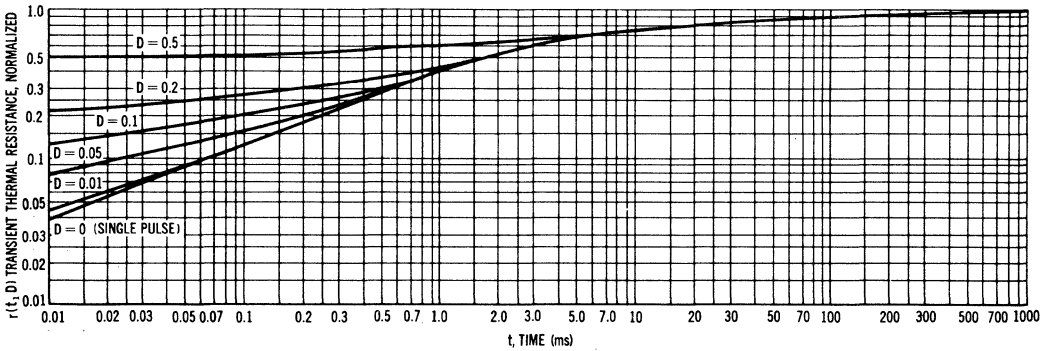
FIGURE 11 — ACTIVE-REGION SAFE OPERATING AREAS



There are two limitations on the power handling ability of a transistor: junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

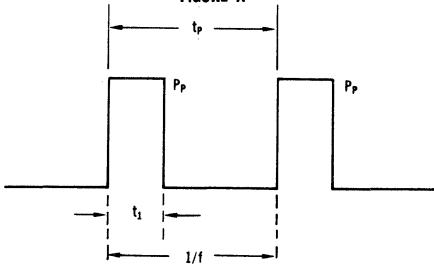
The data of Figure 11 is based on  $T_{J(pk)} = 200^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} < 200^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 12. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

FIGURE 12 — TRANSIENT THERMAL RESISTANCE



DESIGN NOTE: USE OF TRANSIENT THERMAL RESISTANCE DATA

FIGURE A



DUTY CYCLE  $D = t_p \cdot f = \frac{t_i}{t_p}$   
 PEAK PULSE POWER =  $P_p$

A train of periodical power pulses can be represented by the model as shown in Figure A. Using the model and the device thermal response, the normalized effective transient thermal resistance of Figure 12 was calculated for various duty cycles.

To find  $\theta_{JC}(t)$ , multiply the value obtained from Figure 12 by the steady state value  $\theta_{JC}$ .

Example:

The 2N4913 is dissipating 100 watts under the following conditions:  $t_i = 0.1$  ms,  $t_p = 0.5$  ms. ( $D = 0.2$ )

Using Figure 12, at a pulse width of 0.1 ms and  $D = 0.2$ , the reading of  $r(t_i, D)$  is 0.28.

The peak rise in junction temperature is therefore

$\Delta T = r(t) \times P_p \times \theta_{JC} = 0.28 \times 100 \times 2.0 = 56^\circ\text{C}$